

NPN RF POWER TRANSISTOR

DESCRIPTION:

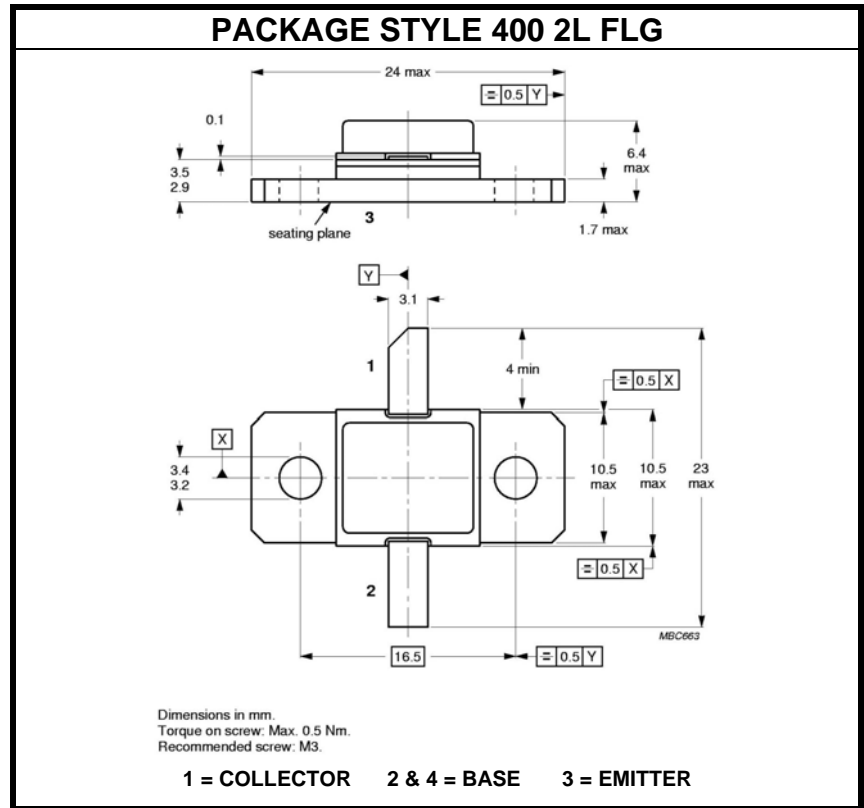
The **AM82731** is a Common Base Device Designed for Pulsed S-Band Radar Amplifier Applications.

FEATURES INCLUDE:

- Input/Output Matching
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	0.9 A
V_{CB0}	50 V
P_{DISS}	27 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	6.5 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 2.0 mA	50			V
BV_{CER}	I _C = 2.0 mA	50			V
I_{CES}	V _{CE} = 2.0 mA			2.0	mA
BV_{EBO}	I _E = 1.0 mA	3.5			V
h_{FE}	V _{CE} = 5 V I _C = 200 mA	10			---
P_G	V _{CE} = 30 V P _{OUT} = 3.0 W f = 2700 to 3100 MHz	5.7	6.5		dB
η_C	Pulse Width = 100 μS Duty Cycle = 10%		35		%